LM118JAN Operational Amplifier

Check for Samples: LM118JAN

FEATURES

- **15 MHz Small Signal Bandwidth**
- **Ensured 50V/µs Slew Rate**
- **Maximum Bias Current of 250 nA**
- **Operates from Supplies of ±5V to ±20V**
- **Internal Frequency Compensation**
- **Input and Output Overload Protected**
- **Pin Compatible with General Purpose Op Amps**

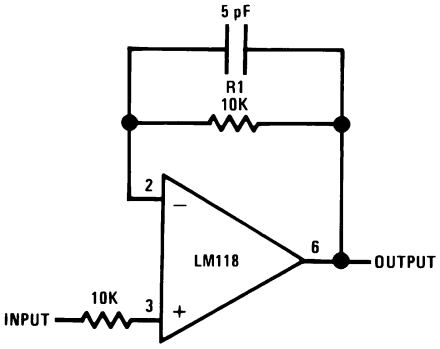
DESCRIPTION

The LM118 is a precision high speed operational amplifier designed for applications requiring wide bandwidth and high slew rate. It features a factor of ten increase in speed over general purpose devices without sacrificing DC performance.

The LM118 has internal unity gain frequency compensation. This considerably simplifies its application since no external components are necessary for operation. However, unlike most internally compensated amplifiers, external frequency compensation may be added for optimum performance. For inverting applications, feed forward compensation will boost the slew rate to over 150V/µs and almost double the bandwidth. Overcompensation can be used with the amplifier for greater stability when maximum bandwidth is not needed. Further, a single capacitor can be added to reduce the 0.1% settling time to under 1 µs.

The high speed and fast settling time of this op amp makes it useful in A/D converters, oscillators, active filters, sample and hold circuits, or general purpose amplifiers. This device is easy to apply and offers an order of magnitude better AC performance than industry standards such as the LM709.

Fast Voltage Follower



Do not hard-wire as voltage follower (R1 ≥ 5 kΩ)

Connection Diagram

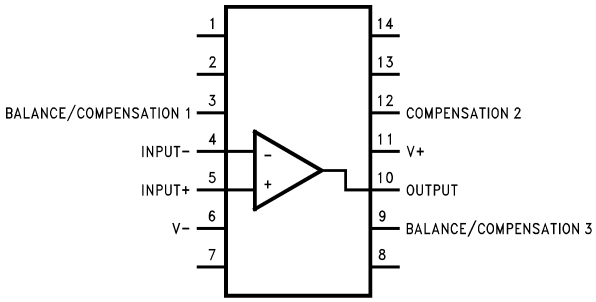
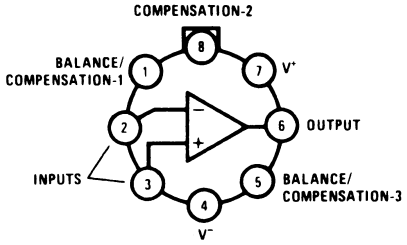


Figure 1. CDIP Package
Top View
See Package Number J0014A



Pin connections shown on schematic diagram and typical applications are for TO-5 package.

Figure 2. TO Package
Top View
See Package Number LMC0008C

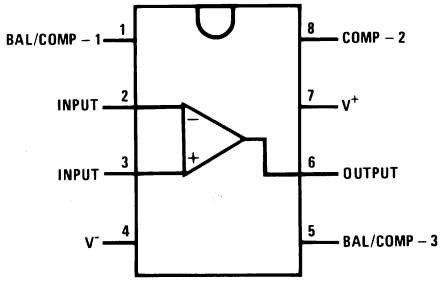


Figure 3. CDIP Package
Top View
See Package Number NAB0008A

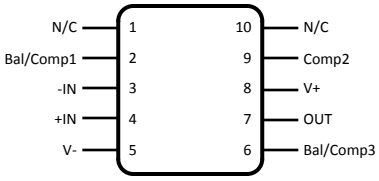
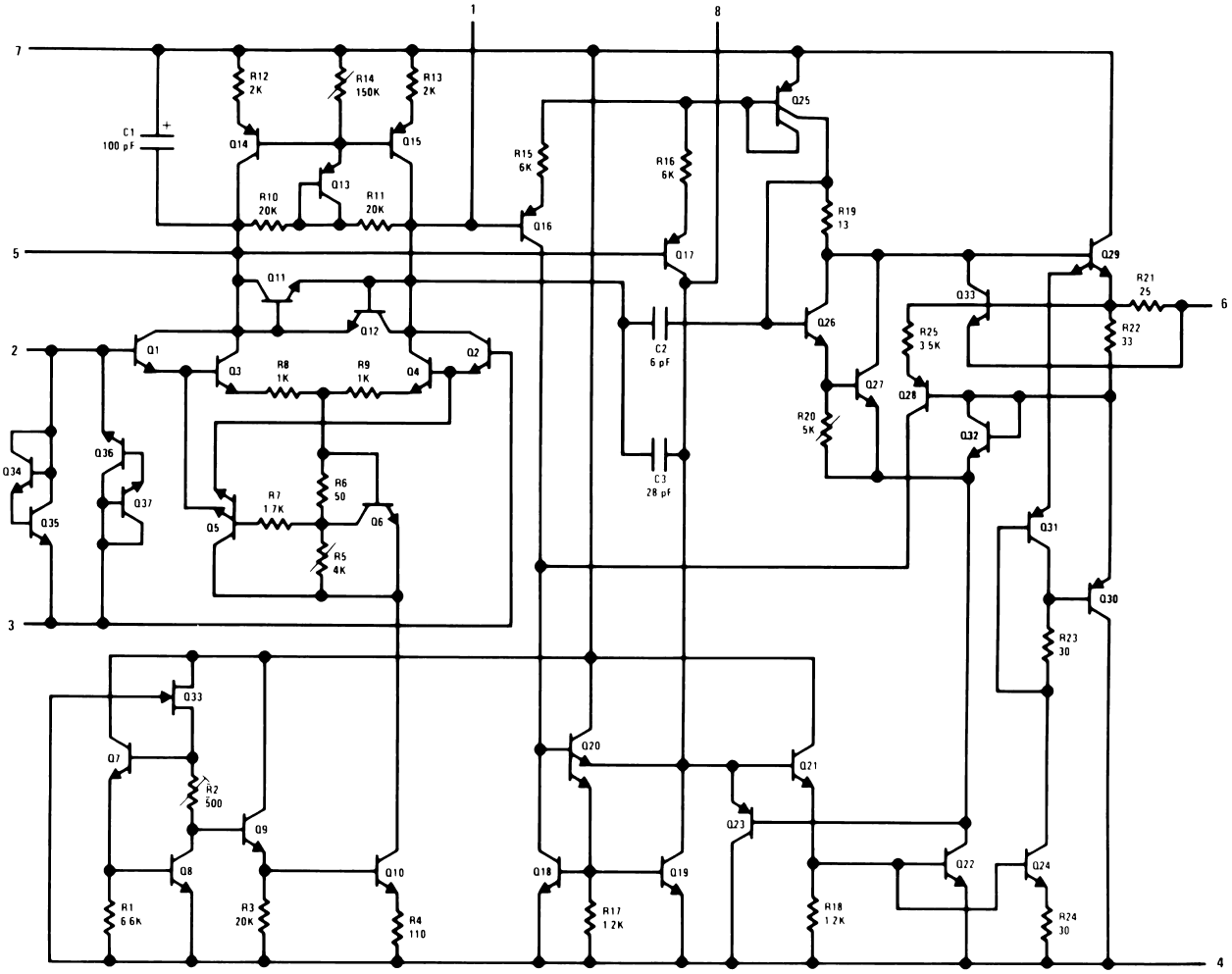


Figure 4. CLGA Package
Top View
See Package Number NAD0010A

Schematic Diagram



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings(1)

Supply Voltage			±20V
Power Dissipation(2)		8 LD TO	750mW
		8LD CDIP	1000mW
		14LD CDIP	1250mW
		10LD CLGA	600mW
Differential Input Current(3)			±10 mA
Input Voltage(4)			±15V
Output Short-Circuit Duration			Continuous
Operating Temperature Range			$-55°C \le T_A \le +125°C$
Thermal Resistance	θ_{JA}	8 LD TO (Still Air @ 0.5W)	160°C/W
		8 LD TO (500LF / Min Air flow @ 0.5W)	86°C/W
		8LD CDIP (Still Air @ 0.5W)	120°C/W
		8LD CDIP (500LF / Min Air flow @ 0.5W)	66°C/W
		14LD CDIP (Still Air @ 0.5W)	87°C/W
		14LD CDIP (500LF / Min Air flow @ 0.5W)	51°C/W
		10LD CLGA (Still Air @ 0.5W)	198°C/W
		10LD CLGA (500LF / Min Air flow @ 0.5W)	124°C/W
	θ_{JC}	8 LD TO	48°C/W
		8LD CDIP	17°C/W
		14LD CDIP	17°C/W
		10LD CLGA	22°C/W
Storage Temperature Range			$-65°C \le T_A \le +150°C$
Lead Temperature (Soldering, 10 seconds)			300°C
ESD Tolerance(5)			2000V

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the Electrical Characteristics. The ensured specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

(2) The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower.

(3) The inputs are shunted with back-to-back diodes for over voltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.

(4) For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.

(5) Human body model, 1.5 kΩ in series with 100 pF.

Quality Conformance Inspection

Mil-Std-883, Method 5005; Group A

Subgroup	Description	Temp°C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55

LM118JAN Electrical Characteristics DC Parameters

The following conditions apply to all the following parameters, unless otherwise specified.

DC: V_{CC} = ±20V

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
V_{IO}	Input Offset Voltage	$+V_{CC}$ = 35V, $-V_{CC}$ = -5V, V_{CM} = -15V		-4.0	4.0	mV	1
				-6.0	6.0	mV	2, 3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -35V, V_{CM} = 15V		-4.0	4.0	mV	1
				-6.0	6.0	mV	2, 3
		V_{CM} = 0V		-4.0	4.0	mV	1
				-6.0	6.0	mV	2, 3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -5V, V_{CM} = 0V		-4.0	4.0	mV	1
				-6.0	6.0	mV	2, 3
I_{IO}	Input Offset Current	$+V_{CC}$ = 35V, $-V_{CC}$ = -5V, V_{CM} = -15V, R_S = 100KΩ	See(1)	-40	40	nA	1
			See(1)	-80	80	nA	2, 3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -35V, V_{CM} = 15V, R_S = 100KΩ	See(1)	-40	40	nA	1
			See(1)	-80	80	nA	2, 3
		V_{CM} = 0V, R_S = 100KΩ	See(1)	-40	40	nA	1
			See(1)	-80	80	nA	2, 3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -5V, V_{CM} = 0V, R_S = 100KΩ	See(1)	-40	40	nA	1
			See(1)	-80	80	nA	2, 3
$\pm I_{IB}$	Input Bias Current	$+V_{CC}$ = 35V, $-V_{CC}$ = -5V, V_{CM} = -15V, R_S = 100KΩ	See(1)	1.0	250	nA	1, 2
			See(1)	1.0	400	nA	3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -35V, V_{CM} = 15V, R_S = 100KΩ	See(1)	1.0	250	nA	1, 2
			See(1)	1.0	400	nA	3
		V_{CM} = 0V, R_S = 100KΩ	See(1)	1.0	250	nA	1, 2
			See(1)	1.0	400	nA	3
		$+V_{CC}$ = 5V, $-V_{CC}$ = -5V, V_{CM} = 0V, R_S = 100KΩ	See(1)	1.0	250	nA	1, 2
			See(1)	1.0	400	nA	3

(1) Slash Sheet: R_S = 20KΩ, tested with R_S = 100KΩ for better resolution.

LM118JAN Electrical Characteristics DC Parameters (continued)

The following conditions apply to all the following parameters, unless otherwise specified.

DC: V_{CC} = ±20V

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
+PSRR	Power Supply Rejection Ratio	+V_{CC} = 10V, -V_{CC} = -20V		-100	100	µV/V	1
				-150	150	µV/V	2, 3
-PSRR	Power Supply Rejection Ratio	+V_{CC} = 20V, -V_{CC} = -10V		-100	100	µV/V	1
				-150	150	µV/V	2, 3
CMRR	Common Mode Rejection Ratio	V_{CM} = ±15V, V_{CC} = ± 35V to ±5V		80		dB	1, 2, 3
+V_{IO} adj.	Offset Null			7.0		mV	1, 2, 3
-V_{IO} adj.	Offset Null				-7.0	mV	1, 2, 3
Delta V_{IO} / Delta T	Temperature Coefficient of Input Offset Voltage	25°C ≤ T_A ≤ 125°C	See(2)	-50	50	µV/°C	2
		-55°C ≤ T_A ≤ 25°C	See(2)	-50	50	µV/°C	3
Delta I_{IO} / Delta T	Temperature Coefficient of Input Offset Current	25°C ≤ T_A ≤ 125°C	See(2)	-1000	1000	pA/°C	2
		-55°C ≤ T_A ≤ 25°C	See(2)	-1000	1000	pA/°C	3
+I_{OS}	Short Circuit Current	+V_{CC} = 15V, -V_{CC} = -15V, t ≤ 25mS, V_{CM} = -15V		-65		mA	1, 2, 3
-I_{OS}	Short Circuit Current	+V_{CC} = 15V, -V_{CC} = -15V, t ≤ 25mS, V_{CM} = 15V			65	mA	1, 2
					80	mA	3
I_{CC}	Power Supply Current	+V_{CC} = 15V, -V_{CC} = -15V			8.0	mA	1
					7.0	mA	2
					9.0	mA	3
+V_{Opp}	Output Voltage Swing	R_L = 10KΩ, V_{CM} = -20V		17		V	4, 5, 6
		R_L = 2KΩ, V_{CM} = -20V		16		V	4, 5, 6
-V_{Opp}	Output Voltage Swing	R_L = 10KΩ, V_{CM} = 20V			-17	V	4, 5, 6
		R_L = 2KΩ, V_{CM} = 20V			-16	V	4, 5, 6
+A_{VS}	Open Loop Voltage Gain	V_O = 15V, R_L = 2KΩ	See(3)	50		V/mV	4
			See(3)	32		V/mV	5, 6
		V_O = 15V, R_L = 10KΩ	See(3)	50		V/mV	4
			See(3)	32		V/mV	5, 6
-A_{VS}	Open Loop Voltage Gain	V_O = -15V, R_L = 2KΩ	See(3)	50		V/mV	4
			See(3)	32		V/mV	5, 6
		V_O = -15V, R_L = 10KΩ	See(3)	50		V/mV	4
			See(3)	32		V/mV	5, 6
A_{VS}	Open Loop Voltage Gain	±V_{CC} = ±5V, V_O = ±2V, R_L = 2KΩ	See(3)	10		V/mV	4, 5, 6
		±V_{CC} = ±5V, V_O = ±2V, R_L = 10KΩ	See(3)	10		V/mV	4, 5, 6

(2) Calculated parameter.
(3) Datalog in K = V/mV

LM118JAN Electrical Characteristics AC Parameters

The following conditions apply to all the following parameters, unless otherwise specified.

AC: V_{CC} = ±20V

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
NI_{BB}	Noise Input Broadband	BW = 10Hz to 5KHz, R_S = 0Ω			25	μV_{RMS}	7
NI_{PC}	Noise Input Popcorn	BW = 10Hz to 5KHz, R_S = 20KΩ			80	μV_{PK}	7
TR_{tR}	Transient Response: Rise Time	V_I = 50mV, PRR = 1KHz			40	nS	7, 8A, 8B
TR_{OS}	Transient Response: Overshoot	V_I = 50mV, PRR = 1KHz			50	%	7, 8A, 8B
+SR	Slew Rate	A_V = 1, V_I = -5V to +5V		50		V/µS	7, 8B
				40		V/µS	8A
-SR	Slew Rate	A_V = 1, V_I = +5V to -5V		50		V/µS	7, 8B
				40		V/µS	8A
$+t_S$	Settling Time	V_I = -5V to +5V	See(1)		800	nS	12
			See(1)		1200	nS	13, 14
$-t_S$	Settling Time	V_I = +5V to -5V	See(1)		800	nS	12
			See(1)		1200	nS	13, 14

(1) Errorband = ±2%.

LM118JAN Electrical Characteristics DC Drift Parameters

The following conditions apply to all the following parameters, unless otherwise specified.

DC: V_{CC} = ±20V

Delta calculations performed on JAN S devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
V_{IO}	Input Offset Voltage	V_{CM} = 0V		-1.0	1.0	mV	1
$±I_{IB}$	Input Bias Current	V_{CM} = 0V, R_S = 100KΩ		-25	25	nA	1

Typical Performance Characteristics

Input Current

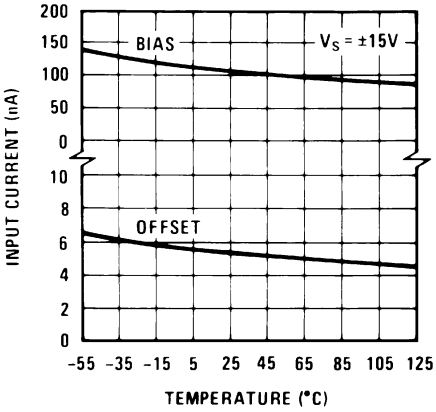


Figure 5.

Voltage Gain

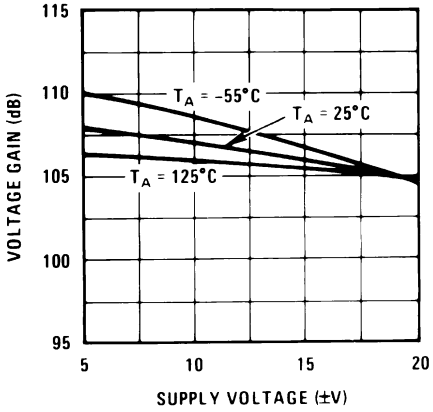


Figure 6.

Power Supply Rejection

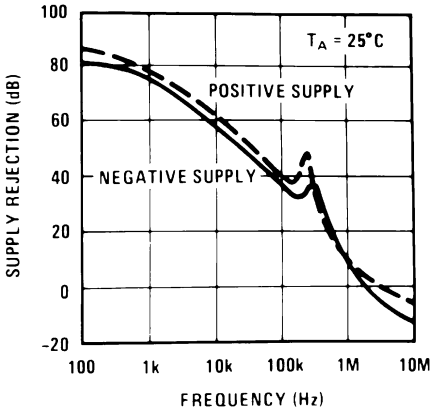


Figure 7.

Input Noise Voltage

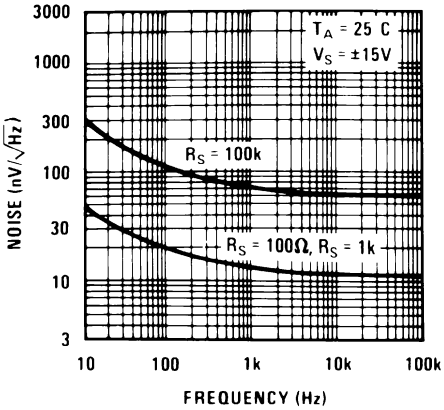


Figure 8.

Common Mode Rejection

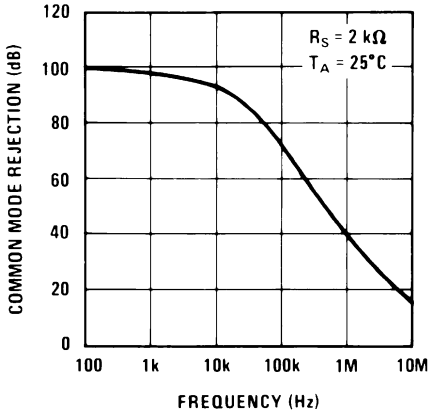


Figure 9.

Supply Current

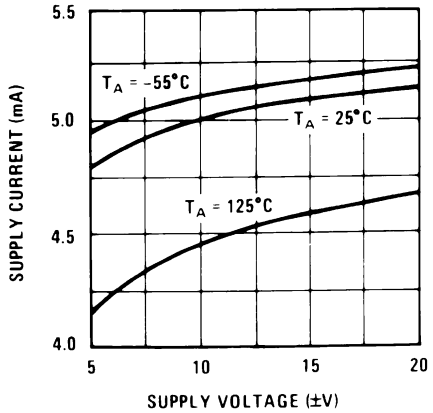


Figure 10.

Typical Performance Characteristics (continued)

Closed Loop Output Impedance

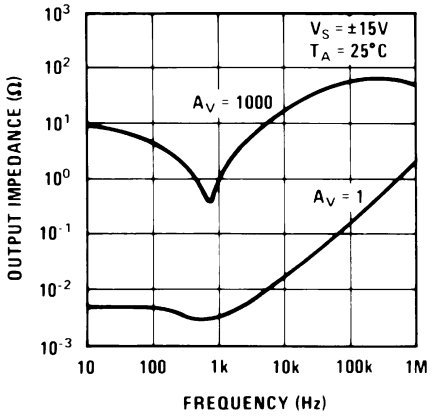


Figure 11.

Current Limiting

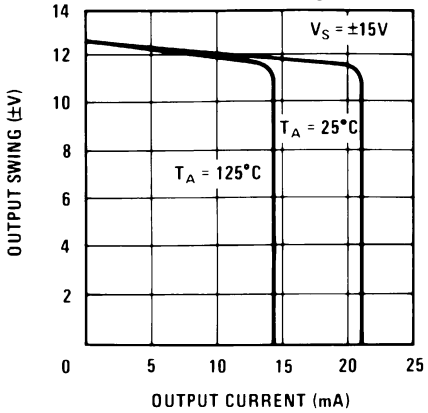


Figure 12.

Input Current

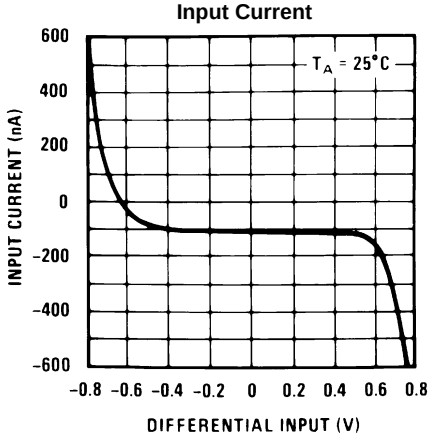


Figure 13.

Unity Gain Bandwidth

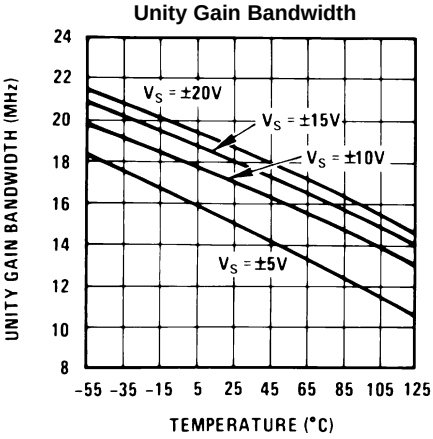


Figure 14.

Voltage Follower Slew Rate

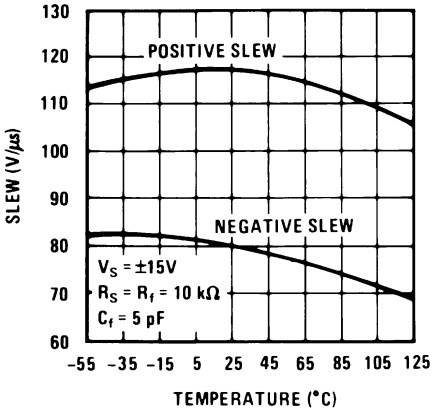


Figure 15.

Inverter Settling Time

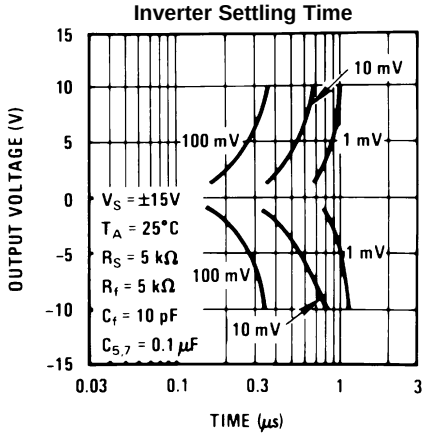


Figure 16.

Typical Performance Characteristics (continued)

Large Signal Frequency Response

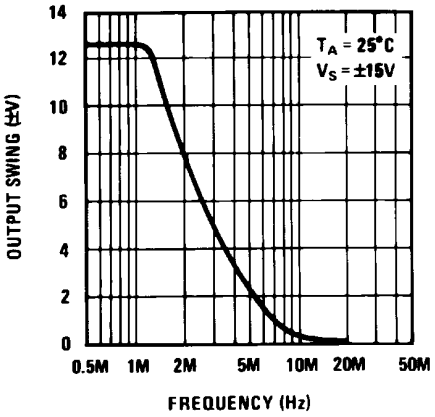


Figure 17.

Open Loop Frequency Response

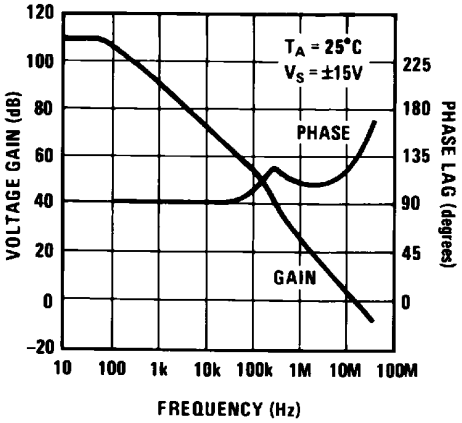


Figure 18.

Voltage Follower Pulse Response

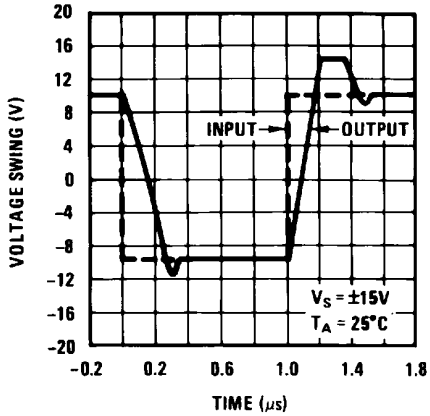


Figure 19.

Large Signal Frequency Response

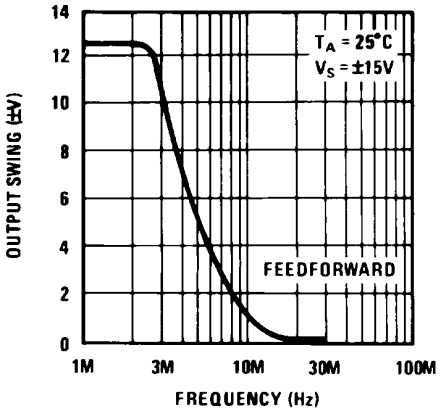


Figure 20.

Open Loop Frequency Response

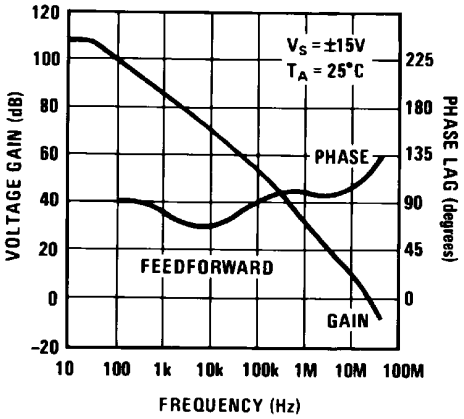


Figure 21.

Inverter Pulse Response

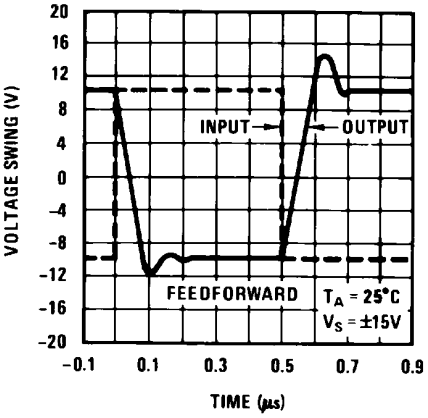
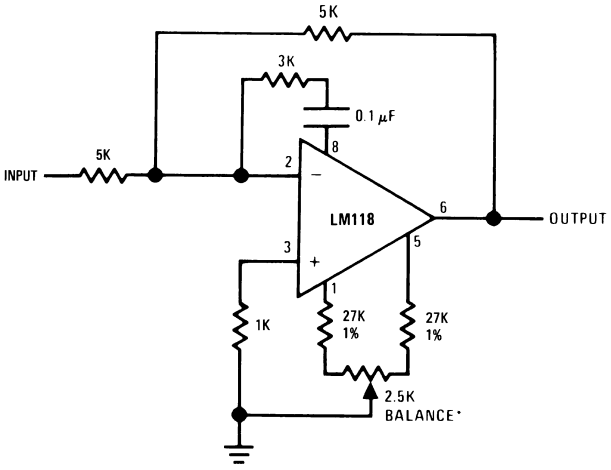


Figure 22.

AUXILIARY CIRCUITS

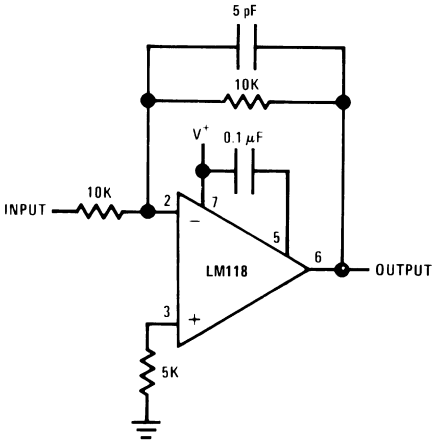
Figure 23. Feedforward Compensation for Greater Inverting Slew Rate



*Balance circuit necessary for increased slew.

Slew rate typically 150V/µs.

Figure 24. Compensation for Minimum Settling Time



Slew and settling time to 0.1% for a 10V step change is 800 ns.

Figure 25. Offset Balancing

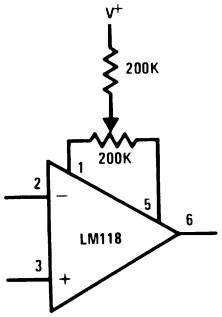


Figure 26. Isolating Large Capacitive Loads

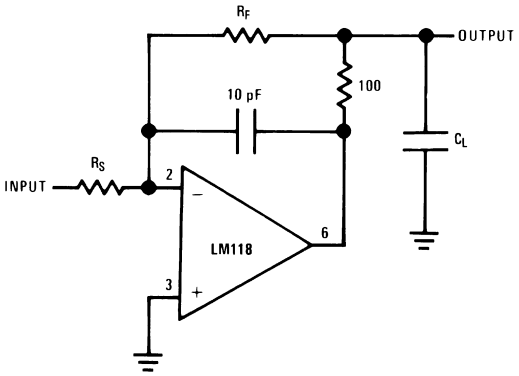
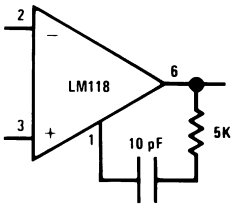


Figure 27. Overcompensation



Typical Applications

Figure 28. Fast Voltage Follower

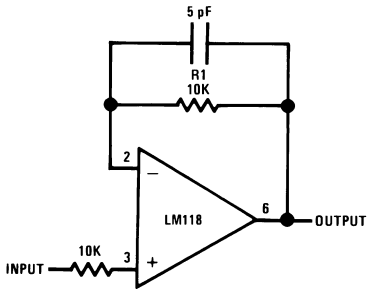
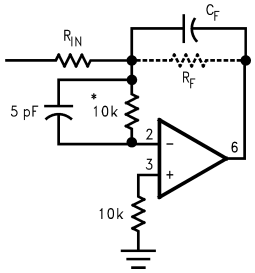


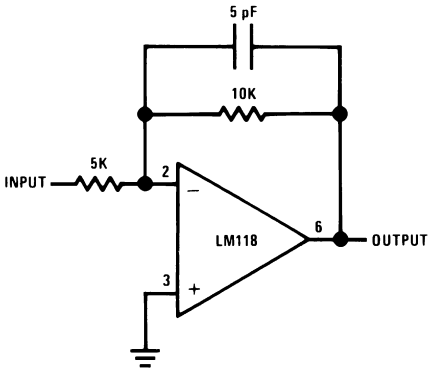
Figure 29. Integrator or Slow Inverter



C_F = Large
(C_F ≥ 50 pF)
*Do not hard-wire as integrator or slow inverter; insert a 10k-5 pF network in series with the input, to prevent oscillation.

(1) Do not hard-wire as voltage follower (R1 ≥ 5 kΩ)

Fast Summing Amplifier



Differential Amplifier

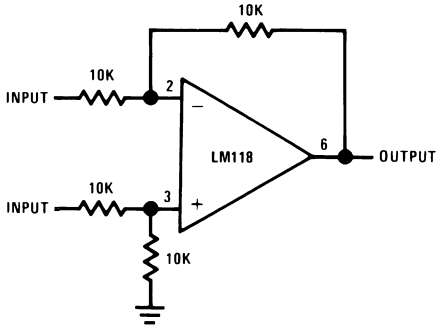


Figure 30. Fast Sample and Hold

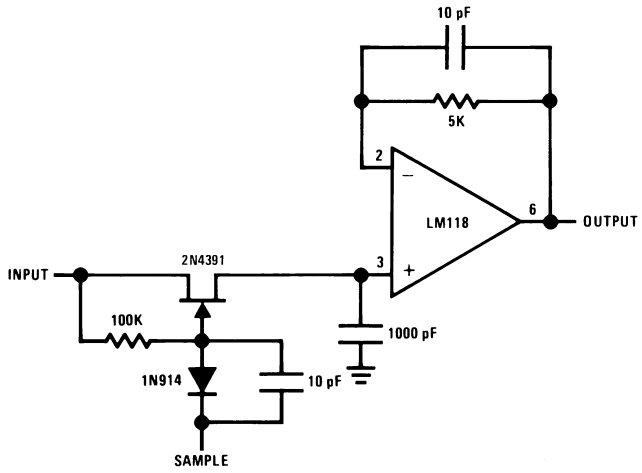
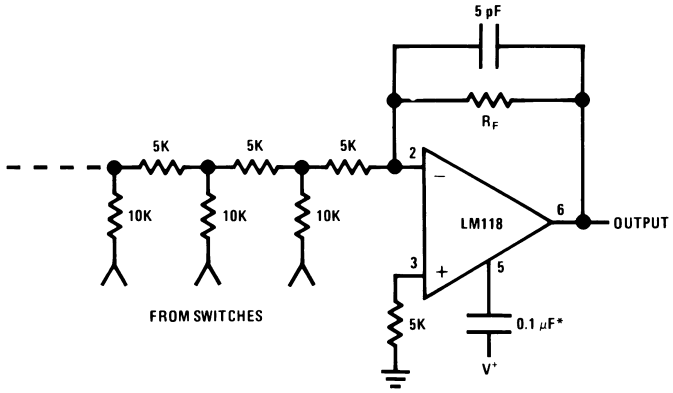
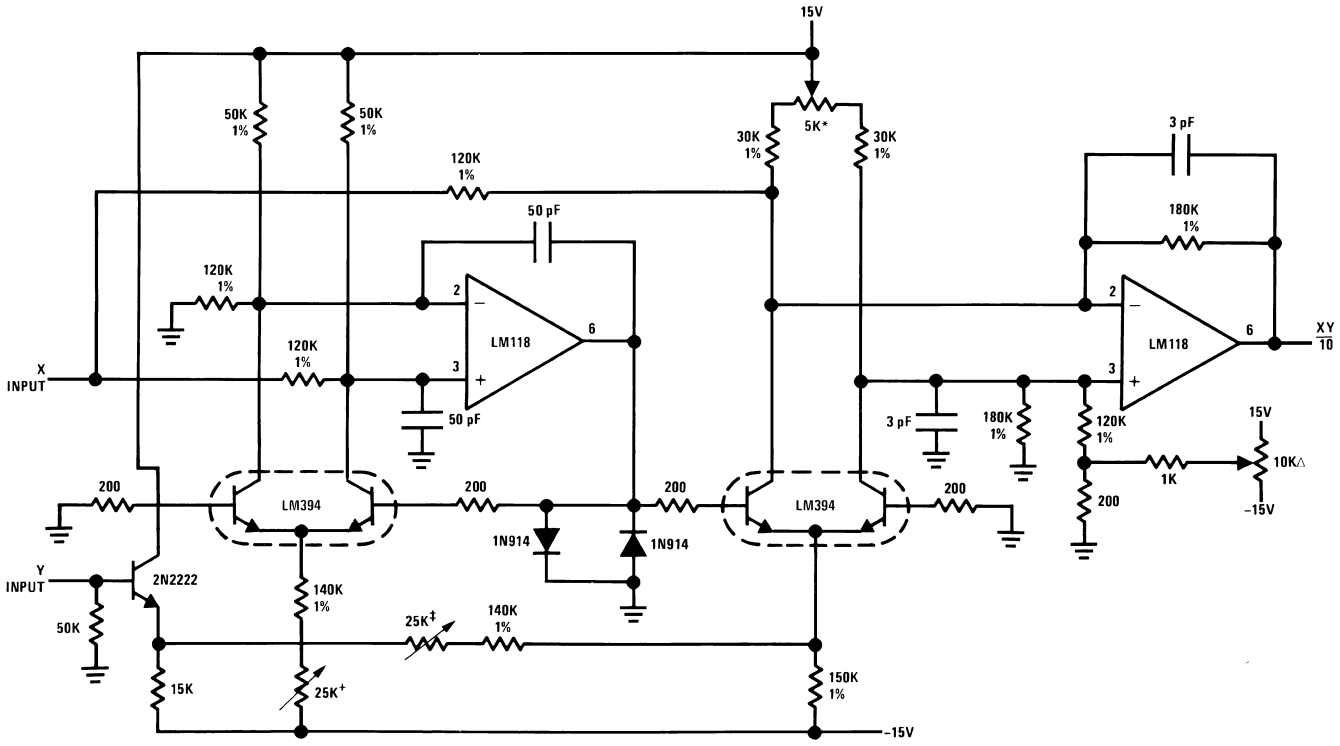


Figure 31. D/A Converter Using Ladder Network



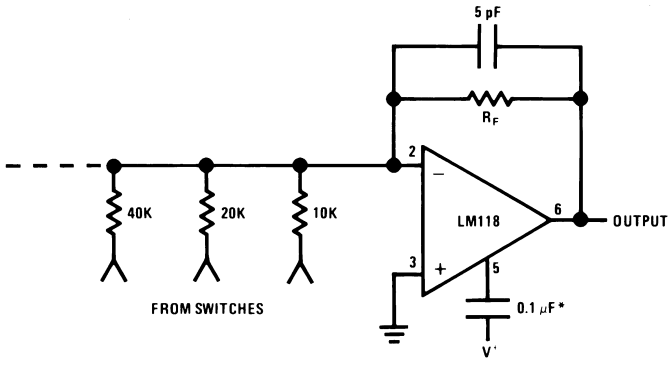
*Optional—Reduces settling time.

Figure 32. Four Quadrant Multiplier



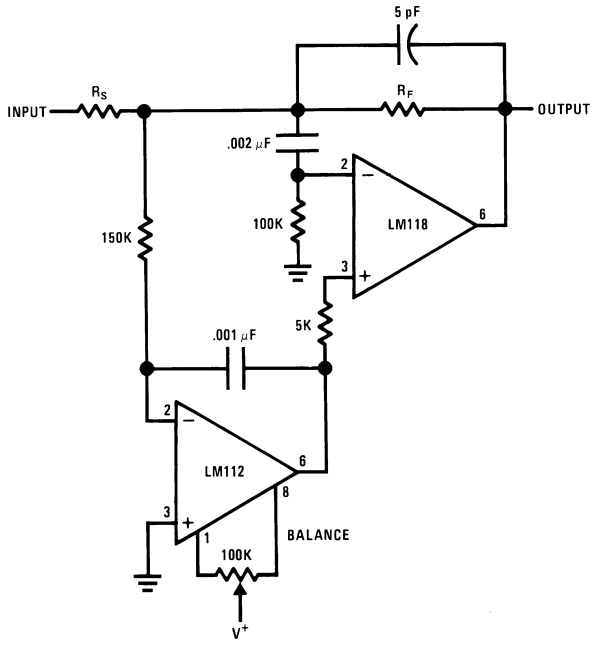
ΔOutput zero.
*"Y" zero
+"X" zero
‡Full scale adjust.

Figure 33. D/A Converter Using Binary Weighted Network

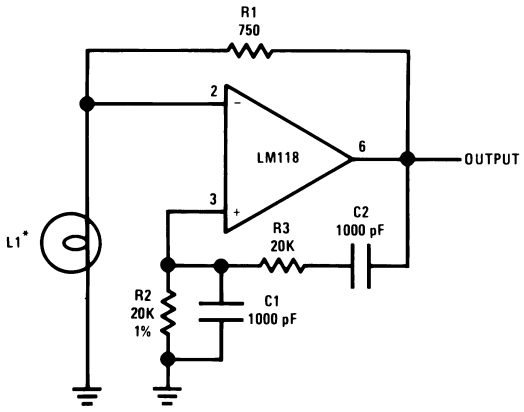


*Optional—Reduces settling time.

Figure 34. Fast Summing Amplifier with Low Input Current



Wein Bridge Sine Wave Oscillator



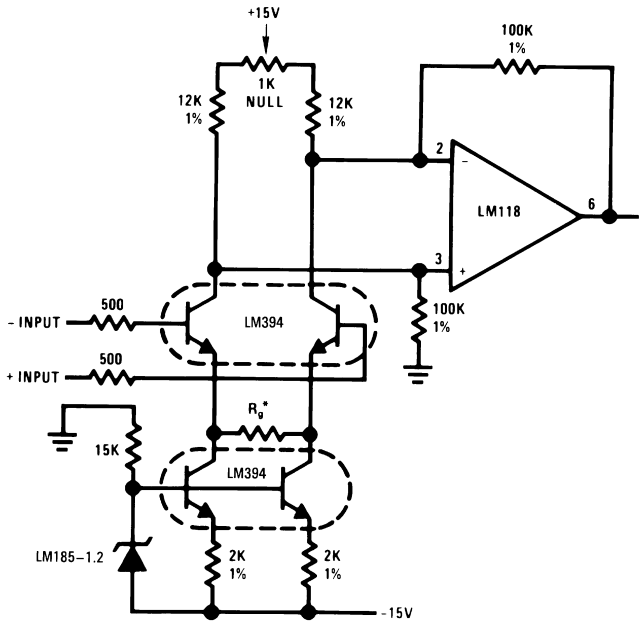
*L1—10V—14 mA bulb ELDEMA 1869

R1 = R2

C1 = C2

$$f = \frac{1}{2\pi R2\, C1}$$

Instrumentation Amplifier



*Gain $\geq \frac{200K}{R_g}$ for $1.5K \leq R_g \leq 200K$

REVISION HISTORY SECTION

Date Released	Revision	Section	Originator	Changes
07/12/05	A	New Release, Corporate format	L. Lytle	1 MDS data sheet, MJLM118–X Rev 0A0 was converted into the Corp. datasheet format. MDS datasheet will be archived.
03/20/2013	A	All Sections		Changed layout of National Data Sheet to TI format

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
JL118BPA	ACTIVE	CDIP	NAB	8	40	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	JL118BPA Q JM38510/ 10107BPA ACO (10107BPA >T, 1010 7BPA MYS)	Samples
M38510/10107BPA	ACTIVE	CDIP	NAB	8	40	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	0 to 0	JL118BPA Q JM38510/ 10107BPA ACO (10107BPA >T, 1010 7BPA MYS)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

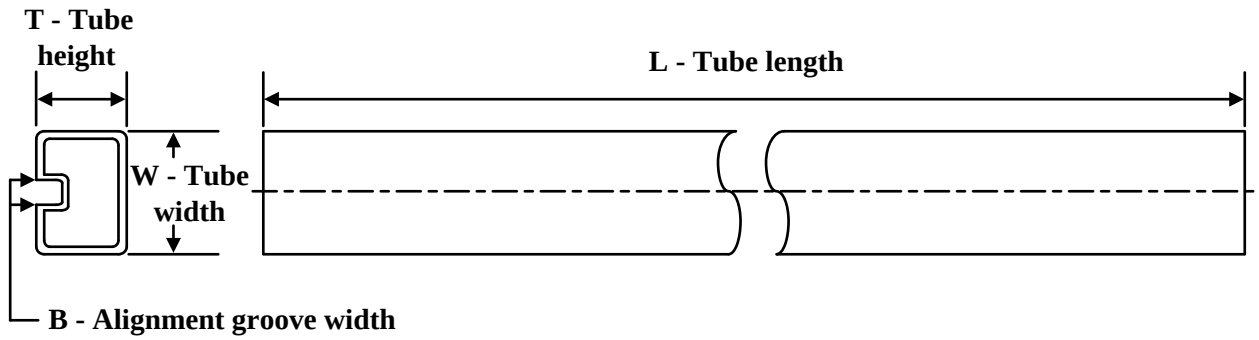
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

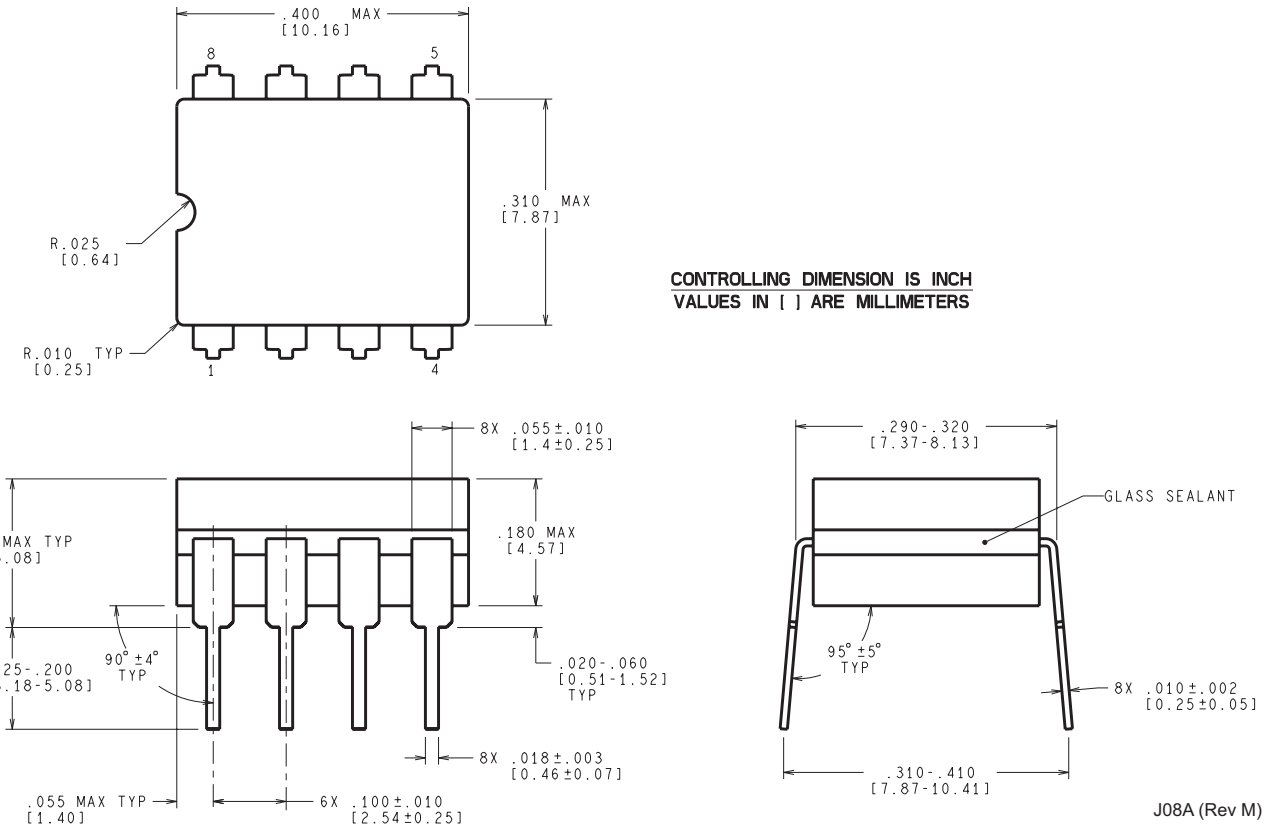
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
JL118BPA	NAB	CDIP	8	40	506.98	15.24	13440	NA
M38510/10107BPA	NAB	CDIP	8	40	506.98	15.24	13440	NA

NAB0008A


.400 MAX
[10.16]
8
5
.310 MAX
[7.87]
R.025
[0.64]
R.010 TYP
[0.25]
1
4
CONTROLLING DIMENSION IS INCH
VALUES IN [ ] ARE MILLIMETERS
8X .055±.010
[1.4±0.25]
.200 MAX TYP
[5.08]
.180 MAX
[4.57]
8X .125-.200
[3.18-5.08]
90° ±4°
TYP
.020-.060
[0.51-1.52]
TYP
8X .018±.003
[0.46±0.07]
.055 MAX TYP
[1.40]
6X .100±.010
[2.54±0.25]
.290-.320
[7.37-8.13]
GLASS SEALANT
95° ±5°
TYP
8X .010±.002
[0.25±0.05]
.310-.410
[7.87-10.41]
J08A (Rev M)

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